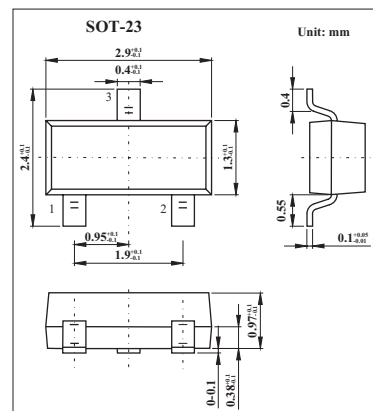


SILICON SWITCHING DIODE

1SS223

■ Features

- Low capacitance: $C_t = 4.0 \text{ pF MAX.}$
- High speed switching: $t_{rr} = 3.0 \text{ ns MAX.}$
- Wide applications including switching, limiter clipper.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	100	V
DC Reverse Voltage	V_R	100	V
Peak Forward Current	I_{FM}	300	mA
Average Rectified Current	I_O	100	mA
DC Forward Current	P	100	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to + 150	$^\circ\text{C}$
Junction to Ambient	$R_{th(j-a)}$	0.67	$^\circ\text{C/mW}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous reverse voltage	V_F	$I_F = 10 \text{ mA}$		720	850	mV
		$I_F = 50 \text{ mA}$		850	1000	
		$I_F = 100 \text{ mA}$		950	1200	
Reverse current	I_R	$V_R = 100 \text{ V}$			1.0	μA
capacitance	C_t	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	4.0	pF
Reverse recovery time	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega$			3.0	ns

■ Marking

Marking	A7
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